## Electronic Supplemental Information (ESI): Tuning of Hole Carrier Density in p-type α-SnWO<sub>4</sub> by Exploiting Oxygen Defects

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Figures S1 to S6



Figure S1. Thermopower versus temperature difference for  $\alpha$ -SnWO<sub>4</sub> samples.



Figure S2. Optical band gaps of α-SnWO<sub>4</sub> samples.



**Figure S3.** Lattice constants of  $\alpha$ -SnWO<sub>4</sub> samples.



Figure S4. Sn/W ratios of α-SnWO<sub>4</sub> samples evaluated using X-ray fluorescence measurements.



**Figure S5.** Plots of intensities of Sn–O and W–O peaks in Sn *K*- and W  $L_3$ -edge EXAFS spectra of  $\alpha$ -SnWO<sub>4</sub> samples, respectively.



Figure S6. Bond lengths of (A) Sn–O(2) and  $O_i$ , (B) W–O(1), O(2), and  $O_i$  of candidate structures shown in Fig. 4.